

PATENT

AMENDMENTS TO THE SPECIFICATION

Please amend the title in all instances as follows:

BIPOLAR TRANSISTOR WITH AN ULTRA SMALL SELF-ALIGNED POLYSILICON  
~~EMITTER AND METHOD OF FORMING THE SILICON GERMANIUM BASE OF THE~~  
TRANSISTOR

Please amend the first paragraph on page 1 as follows:

*Ed.* ~~The present application~~ <sup>Pat. 6,253,234</sup> This is a divisional application of Application Serial No. 09/994,293 filed on November 26, 2002, <sup>Pat. 6,649,482</sup> which is a continuation-in-part of Application Serial No. 09/882,740 filed June 15, 2001, by Abdalla Aly Naem for Bipolar Transistor with a Silicon Germanium Base and an Ultra Small Self-Aligned Polysilicon Emitter and Method of Forming the Transistor.